IN THE CLAIMS:

1. (Currently Amended) A semiconductor device comprising:

a semiconductor IC chip ~~provided with an electrode pad~~ comprising a plurality of electrode pads, said pads each having a side;

an insulating layer ~~formed~~ located on a surface of the semiconductor IC chip, on ~~the side of~~a surface of each of the electrode pads;

a connecting terminal on an outer surface of the insulating layer; and

a conductive post extending through the insulating layer and connecting the electrode pad of the semiconductor IC chip to the connecting ~~terminal;~~terminal,

wherein the insulating layer ~~is formed of~~comprises an insulating elastic material and the conductive post comprises a conductive elastic material.

2. (Canceled)

3. (Currently Amended) The semiconductor device according to claim ~~2~~1, wherein

the ~~conductive elastic material of the conductive post contains~~conductive post comprises a synthetic rubber and conductive particles dispersed in the synthetic rubber.

4. (Currently Amended) The semiconductor device according to claim 3, wherein

the conductive elastic material of the conductive post ~~is~~ comprises a composite paste ~~containing~~ comprising an addition-polymerized silicone rubber, and at least 70% by weight ~~or above~~ Ag particles dispersed in the addition-polymerized silicone rubber, and

the composite paste ~~as~~ when cured has a volume resistivity of not more than 5×10^{-3} $\Omega\cdot$cm ~~or below~~.

5. (Currently Amended) The semiconductor device according to claim 1, ~~wherein~~further comprising:

a wiring layer ~~is formed~~located between ~~the~~ an electrode pad of the semiconductor IC chip and the conductive post.

6. (Currently Amended) The semiconductor device according to claim 1, ~~wherein~~ further comprising:

a wiring part ~~is formed~~located between the connecting terminal and the conductive post.

7. (Original) The semiconductor device according to claim 1, wherein the connecting terminal is a solder ball.

8. (Currently Amended) The semiconductor device according to claim 7, ~~wherein~~ further comprising:

a barrier metal layer ~~is provided~~located between the solder ball and the conductive post.

9. (Currently Amended) The semiconductor device according to claim 1, wherein

the insulating elastic material of the insulating layer is ~~any one~~selected from the group consisting of silicone rubber, fluororubber, polyurethane rubber, polybutadiene rubber,

acrylonitrile-butadiene copolymer and polyisoprene rubber, and has an elastic modulus of not more than 100 MPa ~~or below~~.

10. (Currently Amended) The semiconductor device according to claim 1, ~~wherein~~further comprising:

a protective layer on the outer surface ~~of the insulating layer~~ of the insulating elastic material ~~is coated with a protective layer~~of the insulating layer, and ~~a part of~~

the connecting terminal ~~lies~~ comprises a portion located at a position on the protective layer.

11. (Currently Amended) The semiconductor device according to claim 10, wherein

the protective layer ~~is formed of~~comprises a material selected from the group consisting of a polyimide resin, a liquid crystalline polymer ~~or~~ and an epoxy solder resist.

12. (Currently Amended) The semiconductor device according to claim 1, ~~whereincomprising:~~

~~the semiconductor device is~~ a wafer-level chip-scale package produced by cutting a wafer ~~with~~ into a plurality of semiconductor IC chips.

13.-17. (Canceled)